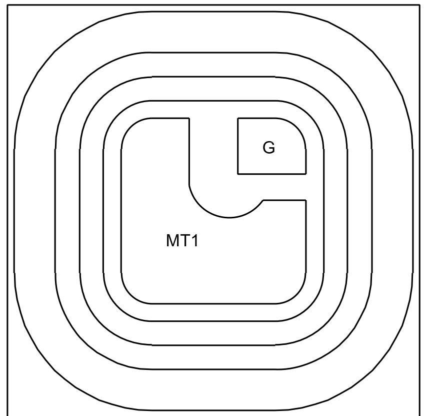
Central™
Semiconductor Corp.

PROCESS CPQ057
TRIAC
2.0 Amp, 600 Volt TRIAC Chip

PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	57 x 57 MILS
Die Thickness	8.6 MILS ± 0.6 MILS
MT1 Bonding Pad Area	28 x 16 MILS
Gate Bonding Pad Area	10 x 9 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE MT2

GROSS DIE PER 4 INCH WAFER
3,374

PRINCIPAL DEVICE TYPES
CQ92-2M
CQ223-2M
CQ89-2M

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